

Dimitris Tsoukalas

List of Publications by Year in descending order

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213
papers

4,178
citations

126708

33
h-index

161609

54
g-index

216
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216
docs citations

216
times ranked

4275
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Breath Analysis: A Promising Tool for Disease Diagnosisâ€”The Role of Sensors. <i>Sensors</i> , 2022, 22, 1238. | 2.1 | 41 |
| 2 | Low Power Stochastic Neurons From SiO ₂ -Based Bilayer Conductive Bridge Memristors for Probabilistic Spiking Neural Network Applicationsâ€”Part II: Modeling. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 2368-2376. | 1.6 | 9 |
| 3 | Low Power Stochastic Neurons From SiO ₂ -Based Bilayer Conductive Bridge Memristors for Probabilistic Spiking Neural Network Applicationsâ€”Part I: Experimental Characterization. <i>IEEE Transactions on Electron Devices</i> , 2022, 69, 2360-2367. | 1.6 | 11 |
| 4 | Chemical Wave Computing from Labware to Electrical Systems. <i>Electronics (Switzerland)</i> , 2022, 11, 1683. | 1.8 | 3 |
| 5 | Memristor-based Oscillator for Complex Chemical Wave Logic Computations: Fredkin Gate Paradigm. , 2022, , . | | 0 |
| 6 | Demonstration of Enhanced Switching Variability and Conductance Quantization Properties in a SiO ₂ Conducting Bridge Resistive Memory with Embedded Two-Dimensional MoS ₂ Material. <i>ACS Applied Electronic Materials</i> , 2022, 4, 2869-2878. | 2.0 | 0 |
| 7 | Material design strategies for emulating neuromorphic functionalities with resistive switching memories. <i>Japanese Journal of Applied Physics</i> , 2022, 61, SM0806. | 0.8 | 4 |
| 8 | Emulating low power nociceptive functionalities with a forming-free SiO ₂ /VO _x conductive bridge memory with Pt nanoparticles. <i>Applied Physics Letters</i> , 2022, 120, . | 1.5 | 5 |
| 9 | Laser-matter interactions. , 2021, , 49-78. | | 2 |
| 10 | Resistive crack-based nanoparticle strain sensors with extreme sensitivity and adjustable gauge factor, made on flexible substrates. <i>Nanoscale</i> , 2021, 13, 3263-3274. | 2.8 | 34 |
| 11 | Emulating artificial neuron and synaptic properties with SiO ₂ -based memristive devices by tuning threshold and bipolar switching effects. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 225303. | 1.3 | 23 |
| 12 | Emulating Artificial Synaptic Plasticity Characteristics from SiO ₂ -Based Conductive Bridge Memories with Pt Nanoparticles. <i>Micromachines</i> , 2021, 12, 306. | 1.4 | 10 |
| 13 | Tuning the analog synaptic properties of forming free SiO ₂ memristors by material engineering. <i>Applied Physics Letters</i> , 2021, 118, . | 1.5 | 20 |
| 14 | Impact of Active Electrode on the Synaptic Properties of SiO ₂ -Based Forming-Free Conductive Bridge Memory. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 1598-1603. | 1.6 | 15 |
| 15 | Simulation tool for predicting and optimizing the performance of nanoparticle based strain sensors. <i>Nanotechnology</i> , 2021, 32, 275501. | 1.3 | 6 |
| 16 | Highly Flexible Artificial Synapses from SiO ₂ -Based Conductive Bridge Memristors and Pt Nanoparticles through a Crack Suppression Technique. <i>ACS Applied Electronic Materials</i> , 2021, 3, 2729-2737. | 2.0 | 7 |
| 17 | Unconventional Logic on Memristor-Based Oscillatory Medium. , 2021, , . | | 1 |
| 18 | Identification of Two Commercial Pesticides by a Nanoparticle Gas-Sensing Array. <i>Sensors</i> , 2021, 21, 5803. | 2.1 | 5 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Emulating artificial mechanoreceptor functionalities from SiO ₂ -based memristor and PDMS stretchable sensor for artificial skin applications. , 2021, , . | | 0 |
| 20 | Multifunctional Spatially-Expanded Logic Gate for Unconventional Computations with Memristor-Based Oscillators. , 2021, , . | | 1 |
| 21 | Memristive Oscillatory Networks for Computing: The Chemical Wave Propagation Paradigm. , 2021, , . | | 5 |
| 22 | Emulating artificial mechanoreceptor functionalities from SiO ₂ -based memristor and PDMS stretchable sensor for artificial skin applications. , 2021, , . | | 0 |
| 23 | Margolus Chemical Wave Logic Gate with Memristive Oscillatory Networks. , 2021, , . | | 3 |
| 24 | A sensing approach for automated and real-time pesticide detection in the scope of smart-farming. Computers and Electronics in Agriculture, 2020, 178, 105759. | 3.7 | 26 |
| 25 | Investigating the origins of ultra-short relaxation times of silver filaments in forming-free SiO ₂ -based conductive bridge memristors. Nanotechnology, 2020, 31, 454002. | 1.3 | 34 |
| 26 | Nanoparticles Synthesised in the Gas-Phase and Their Applications in Sensors: A Review. Applied Nano, 2020, 1, 70-86. | 0.9 | 6 |
| 27 | Thin Film Protected Flexible Nanoparticle Strain Sensors: Experiments and Modeling. Sensors, 2020, 20, 2584. | 2.1 | 11 |
| 28 | Spatial Confinement Effects of Embedded Nanocrystals on Multibit and Synaptic Properties of Forming Free SiO ₂ -Based Conductive Bridge Random Access Memory. IEEE Electron Device Letters, 2020, 41, 1013-1016. | 2.2 | 13 |
| 29 | Enhancing the synaptic properties of low-power and forming-free HfO _x /TaO _y /HfO _x resistive switching devices. Microelectronic Engineering, 2020, 229, 111358. | 1.1 | 22 |
| 30 | Impact of Pt embedded nanocrystals on the resistive switching and synaptic properties of forming free TiO ₂ /TiO ₂ -based bilayer structures. Journal of Applied Physics, 2019, 126, . | 1.1 | 24 |
| 31 | Tungsten doping effect on V ₂ O ₅ thin film electrochromic performance. Electrochimica Acta, 2019, 321, 134743. | 2.6 | 47 |
| 32 | Impedimetric nanoparticle aptasensor for selective and label free pesticide detection. Microelectronic Engineering, 2018, 189, 39-45. | 1.1 | 47 |
| 33 | Plasma induced degradation and surface electronic structure modification of Poly(3-hexylthiophene) films. Polymer Degradation and Stability, 2018, 149, 162-172. | 2.7 | 7 |
| 34 | Tuning Resistive, Capacitive, and Synaptic Properties of Forming Free TiO ₂ -Based RRAM Devices by Embedded Pt and Ta Nanocrystals. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700440. | 0.8 | 12 |
| 35 | A highly sensitive impedimetric aptasensor for the selective detection of acetamiprid and atrazine based on microwires formed by platinum nanoparticles. Biosensors and Bioelectronics, 2018, 101, 268-274. | 5.3 | 115 |
| 36 | Coalescence of Cluster Beam Generated Sub-2 nm Bare Au Nanoparticles and Analysis of Au Film Growth Parameters. Annalen Der Physik, 2018, 530, 1700256. | 0.9 | 2 |

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|----|---|-----|-----------|
| 37 | Nanoparticle based gas-sensing array for pesticide detection. Journal of Environmental Chemical Engineering, 2018, 6, 6641-6646. | 3.3 | 13 |
| 38 | Atomic layer deposited Al ₂ O ₃ thin films as humidity barrier coatings for nanoparticle-based strain sensors. Nanotechnology, 2018, 29, 465706. | 1.3 | 11 |
| 39 | Synthesis of hafnium nanoparticles and hafnium nanoparticle films by gas condensation and energetic deposition. Beilstein Journal of Nanotechnology, 2018, 9, 1868-1880. | 1.5 | 6 |
| 40 | Oxygen and temperature effects on the electrochemical and electrochromic properties of rf-sputtered V ₂ O ₅ thin films. Electrochimica Acta, 2017, 232, 54-63. | 2.6 | 40 |
| 41 | Investigating the origins of high multilevel resistive switching in forming free Ti/TiO ₂ ^x -based memory devices through experiments and simulations. Journal of Applied Physics, 2017, 121, . | 1.1 | 32 |
| 42 | Resistive memory multilayer structure with self-rectifying and forming free properties along with their modification by adding a hafnium nanoparticle midlayer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, . | 0.9 | 3 |
| 43 | Low-Power Forming Free TiO ₂ ^x /HfO ₂ ^y /TiO ₂ ^x RRAM Devices Exhibiting Synaptic Property Characteristics. IEEE Transactions on Electron Devices, 2017, 64, 3151-3158. | 1.6 | 43 |
| 44 | Coexistence of bipolar and threshold resistive switching in TiO ₂ -based structure with embedded hafnium nanoparticles. Journal Physics D: Applied Physics, 2017, 50, 045103. | 1.3 | 11 |
| 45 | Tunable Properties of Mg-Doped V ₂ O ₅ Thin Films for Energy Applications: Li-Ion Batteries and Electrochromics. Journal of Physical Chemistry C, 2017, 121, 70-79. | 1.5 | 82 |
| 46 | Ultra-Low Power Multilevel Switching with Enhanced Uniformity in Forming Free TiO ₂ ^x -Based RRAM with Embedded Pt Nanocrystals. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700570. | 0.8 | 25 |
| 47 | Experiments and simulation of multilevel resistive switching in forming free Ti/TiO ₂ ^x RRAM devices. , 2017, , . | | 2 |
| 48 | Heavy metal ion detection using DNAzyme-modified platinum nanoparticle networks. Sensors and Actuators B: Chemical, 2017, 239, 962-969. | 4.0 | 25 |
| 49 | Low temperature rf-sputtered thermochromic VO ₂ films on flexible glass substrates. Advanced Materials Letters, 2017, 8, 757-761. | 0.3 | 16 |
| 50 | Nanoparticles-Based Flash-Like Nonvolatile Memories: Cluster Beam Synthesis of Metallic Nanoparticles and Challenges for the Overlying Control Oxide Layer. , 2017, , 157-210. | | 0 |
| 51 | Understanding the Formation of Conducting Filaments in RRAM Through the Design of Experiments. , 2017, , . | | 0 |
| 52 | Vectorial strain gauge method using single flexible orthogonal polydimethylsiloxane gratings. Scientific Reports, 2016, 6, 23606. | 1.6 | 19 |
| 53 | Understanding the Formation of Conducting Filaments in RRAM Through the Design of Experiments. International Journal of High Speed Electronics and Systems, 2016, 25, 1640007. | 0.3 | 5 |
| 54 | Engineering amorphous-crystalline interfaces in TiO ₂ ^x /TiO ₂ ^y -based bilayer structures for enhanced resistive switching and synaptic properties. Journal of Applied Physics, 2016, 120, . | 1.1 | 38 |

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|----|---|-----|-----------|
| 55 | Thermochromic performance of Mg-doped VO ₂ thin films on functional substrates for glazing applications. <i>Solar Energy Materials and Solar Cells</i> , 2016, 157, 1004-1010. | 3.0 | 60 |
| 56 | Physical modelling of the SET/RESET characteristics and analog properties of TiO _x /HfO ₂ ^x /TiO _x -based RRAM devices. , 2016, , . | | 2 |
| 57 | Low-Power and Highly Uniform 3-b Multilevel Switching in Forming Free TiO ₂ -Based RRAM With Embedded Pt Nanocrystals. <i>IEEE Electron Device Letters</i> , 2016, 37, 874-877. | 2.2 | 59 |
| 58 | Label-free DNA biosensor based on resistance change of platinum nanoparticles assemblies. <i>Biosensors and Bioelectronics</i> , 2016, 81, 388-394. | 5.3 | 18 |
| 59 | Facile synthesis of core-shell structured PANI-Co ₃ O ₄ nanocomposites with superior electrochemical performance in supercapacitors. <i>Applied Surface Science</i> , 2016, 361, 57-62. | 3.1 | 106 |
| 60 | Highly Stretchable Electrodes on Wrinkled Polydimethylsiloxane Substrates. <i>Scientific Reports</i> , 2015, 5, 16527. | 1.6 | 101 |
| 61 | Millisecond non-melt laser annealing of phosphorus implanted germanium: Influence of nitrogen co-doping. <i>Journal of Applied Physics</i> , 2015, 118, . | 1.1 | 22 |
| 62 | Memory programming of TiO ₂ ^x films by Conductive Atomic Force Microscopy evidencing filamentary resistive switching. <i>Applied Surface Science</i> , 2015, 332, 55-61. | 3.1 | 24 |
| 63 | The effect of buffer layer on the thermochromic properties of undoped radio frequency sputtered VO ₂ thin films. <i>Thin Solid Films</i> , 2015, 594, 310-315. | 0.8 | 24 |
| 64 | Wrinkled Ag nanostructured gratings towards single molecule detection by ultrahigh surface Raman scattering enhancement. <i>Sensors and Actuators B: Chemical</i> , 2015, 218, 145-151. | 4.0 | 34 |
| 65 | Material and Device Parameters Influencing Multi-Level Resistive Switching of Room Temperature Crown Titanium Oxide Layers. <i>Materials Research Society Symposia Proceedings</i> , 2015, 1729, 59-64. | 0.1 | 0 |
| 66 | Improving the resistive switching uniformity of forming-free TiO ₂ and Pt based devices by embedded Pt nanocrystals. , 2015, , . | | 5 |
| 67 | Structural Characterization of Layers for Advanced Non-volatile Memories. <i>Springer Proceedings in Physics</i> , 2015, , 9-17. | 0.1 | 0 |
| 68 | CO_2 Laser Annealing for USJ Formation in Silicon: Comparison of Simulation and Experiment. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 696-701. | 1.6 | 9 |
| 69 | Influence of oxygen content of room temperature TiO ₂ deposited films for enhanced resistive switching memory performance. <i>Journal of Applied Physics</i> , 2014, 115, 034516. | 1.1 | 47 |
| 70 | Novel conducting polymer current limiting devices for low cost surge protection applications. <i>Journal of Applied Physics</i> , 2014, 116, 164501. | 1.1 | 5 |
| 71 | ZnO nanoparticles embedded in polyethylene-glycol (PEG) matrix as sensitive strain gauge elements. <i>Journal of Nanoparticle Research</i> , 2014, 16, 1. | 0.8 | 5 |
| 72 | Picosecond and nanosecond laser annealing and simulation of amorphous silicon thin films for solar cell applications. <i>Journal of Applied Physics</i> , 2014, 115, 043108. | 1.1 | 17 |

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| 73 | Influence of Ti top electrode thickness on the resistive switching properties of forming free and self-rectified TiO ₂ thin films. <i>Thin Solid Films</i> , 2014, 571, 23-31. | 0.8 | 33 |
| 74 | Cluster beam synthesis of metal and metal-oxide nanoparticles for emerging memories. <i>Solid-State Electronics</i> , 2014, 101, 95-105. | 0.8 | 12 |
| 75 | Flexible platinum nanoparticle strain sensors. , 2013, , . | | 2 |
| 76 | Flexible polyimide chemical sensors using platinum nanoparticles. <i>Sensors and Actuators B: Chemical</i> , 2013, 189, 106-112. | 4.0 | 29 |
| 77 | Laser printing and characterization of semiconducting polymers for organic electronics. <i>Applied Physics A: Materials Science and Processing</i> , 2013, 110, 559-563. | 1.1 | 20 |
| 78 | Nickel nanoparticle size and density effects on non-volatile memory performance. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, . | 0.6 | 8 |
| 79 | Investigation of the gate oxide leakage current of low temperature formed hafnium oxide films. <i>Journal of Applied Physics</i> , 2013, 113, . | 1.1 | 13 |
| 80 | Forming-free resistive switching memories based on titanium-oxide nanoparticles fabricated at room temperature. <i>Applied Physics Letters</i> , 2013, 102, 022909. | 1.5 | 31 |
| 81 | Inorganic Nanoparticles for either Charge Storage or Memristance Modulation. <i>Advances in Science and Technology</i> , 2012, 77, 196-204. | 0.2 | 0 |
| 82 | PHEMA functionalization of gold nanoparticles for vapor sensing: Chemi-resistance, chemi-capacitance and chemi-impedance. <i>Sensors and Actuators B: Chemical</i> , 2012, 170, 129-136. | 4.0 | 24 |
| 83 | Resistive switching memory using titanium-oxide nanoparticle films. , 2012, , . | | 0 |
| 84 | High strain sensitivity controlled by the surface density of platinum nanoparticles. <i>Nanotechnology</i> , 2012, 23, 285501. | 1.3 | 55 |
| 85 | Chemical sensing based on double layer PHEMA polymer and platinum nanoparticle films. <i>Sensors and Actuators B: Chemical</i> , 2012, 175, 85-91. | 4.0 | 12 |
| 86 | Platinum Nanoparticle Chemical Sensors on Polyimide Substrates. <i>Procedia Engineering</i> , 2012, 47, 778-781. | 1.2 | 1 |
| 87 | Surface functionalization studies and direct laser printing of oligonucleotides toward the fabrication of a micromembrane DNA capacitive biosensor. <i>Sensors and Actuators B: Chemical</i> , 2012, 175, 123-131. | 4.0 | 25 |
| 88 | Modeling of charge-trapping non-volatile-memories based on HfO ₂ . <i>Microelectronic Engineering</i> , 2012, 90, 23-25. | 1.1 | 9 |
| 89 | Evaluation of capacitive surface stress biosensors. <i>Microelectronic Engineering</i> , 2012, 90, 37-39. | 1.1 | 6 |
| 90 | Electrostatic self-assembly of nanoparticles into ordered nanowire arrays. <i>Journal of Materials Research</i> , 2011, 26, 209-214. | 1.2 | 4 |

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| 91 | Two-dimensional nanoparticle self-assembly using plasma-induced Ostwald ripening. <i>Nanotechnology</i> , 2011, 22, 235306. | 1.3 | 18 |
| 92 | Size control of Ag nanoparticles for SERS sensing applications. <i>Procedia Engineering</i> , 2011, 25, 280-283. | 1.2 | 7 |
| 93 | Nanoparticle Strain Sensor. <i>Procedia Engineering</i> , 2011, 25, 635-638. | 1.2 | 17 |
| 94 | Chemi-resistive sensors based on platinum nanoparticle arrays. <i>Procedia Engineering</i> , 2011, 25, 1129-1132. | 1.2 | 1 |
| 95 | Raman enhancement of rhodamine adsorbed on Ag nanoparticles self-assembled into nanowire-like arrays. <i>Nanoscale Research Letters</i> , 2011, 6, 629. | 3.1 | 16 |
| 96 | ZnO nanoparticles produced by novel reactive physical deposition process. <i>Applied Surface Science</i> , 2011, 257, 5366-5369. | 3.1 | 11 |
| 97 | Optimization of hafnium oxide for use in nanoparticle memories. <i>Microelectronic Engineering</i> , 2011, 88, 1189-1193. | 1.1 | 15 |
| 98 | Chemiresistive sensor fabricated by the sequential ink-jet printing deposition of a gold nanoparticle and polymer layer. <i>Microelectronic Engineering</i> , 2010, 87, 2258-2263. | 1.1 | 20 |
| 99 | Non-melting annealing of silicon by CO2 laser. <i>Thin Solid Films</i> , 2010, 518, 2551-2554. | 0.8 | 6 |
| 100 | Trapping properties of sputtered hafnium oxide films: Bulk traps vs. interface traps. <i>Thin Solid Films</i> , 2010, 518, 5579-5584. | 0.8 | 11 |
| 101 | A chemical sensor microarray realized by laser printing of polymers. <i>Sensors and Actuators B: Chemical</i> , 2010, 150, 148-153. | 4.0 | 26 |
| 102 | Formation of silicon ultra shallow junction by non-melt excimer laser treatment. <i>Solid-State Electronics</i> , 2010, 54, 903-908. | 0.8 | 5 |
| 103 | Detection of DNA mutations using a capacitive micro-membrane array. <i>Biosensors and Bioelectronics</i> , 2010, 26, 1588-1592. | 5.3 | 19 |
| 104 | Sensitivity investigations of surface stress capacitive DNA sensor. , 2010, , . | | 0 |
| 105 | Experiments and simulation on diffusion and activation of codoped with arsenic and phosphorous germanium. <i>Journal of Applied Physics</i> , 2010, 108, 024903. | 1.1 | 25 |
| 106 | Modeling and experiments on diffusion and activation of phosphorus in germanium. <i>Journal of Applied Physics</i> , 2009, 105, 094910. | 1.1 | 41 |
| 107 | Metallic nanoparticles for application in electronic non-volatile memories. <i>International Journal of Nanotechnology</i> , 2009, 6, 35. | 0.1 | 11 |
| 108 | Detection of the biotin-streptavidin interaction by exploiting surface stress changes on ultrathin Si membranes. <i>Microelectronic Engineering</i> , 2009, 86, 1495-1498. | 1.1 | 16 |

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| 109 | Selective deposition of charged nanoparticles by self-electric focusing effect. <i>Microelectronic Engineering</i> , 2009, 86, 898-901. | 1.1 | 4 |
| 110 | Fabrication of gold nanoparticle lines based on fracture induced patterning. <i>Microelectronic Engineering</i> , 2009, 86, 861-864. | 1.1 | 4 |
| 111 | Assembly of charged nanoparticles using self-electrodynamic focusing. <i>Nanotechnology</i> , 2009, 20, 365605. | 1.3 | 19 |
| 112 | From silicon to organic nanoparticle memory devices. <i>Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences</i> , 2009, 367, 4169-4179. | 1.6 | 23 |
| 113 | Investigation of top gate electrode options for high- κ gate dielectric MOS capacitors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3626-3629. | 0.8 | 0 |
| 114 | Deposition and electrical characterization of hafnium oxide films on silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3720-3723. | 0.8 | 8 |
| 115 | Design and fabrication of a Si micromechanical capacitive array for DNA sensing. <i>Microelectronic Engineering</i> , 2008, 85, 1359-1361. | 1.1 | 11 |
| 116 | Non-melt laser annealing of Plasma Implanted Boron for ultra shallow junctions in Silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 154-155, 39-42. | 1.7 | 17 |
| 117 | Diffusion and activation of phosphorus in germanium. <i>Materials Science in Semiconductor Processing</i> , 2008, 11, 372-377. | 1.9 | 14 |
| 118 | High-density plasma silicon oxide thin films grown at room-temperature. <i>Microelectronic Engineering</i> , 2008, 85, 1245-1247. | 1.1 | 2 |
| 119 | Electrical behavior of memory devices based on fluorene-containing organic thin films. <i>Journal of Applied Physics</i> , 2008, 104, 044510. | 1.1 | 30 |
| 120 | Development of Wireless Pressure Measurement System for Short Range medical Applications. , 2007, , . | | 2 |
| 121 | Deposition Of Uniform Size Metallic Nanoparticles For Use In Non Volatile Memories. <i>Materials Research Society Symposia Proceedings</i> , 2007, 997, 1. | 0.1 | 1 |
| 122 | Electronic memory device based on a single-layer fluorene-containing organic thin film. <i>Applied Physics Letters</i> , 2007, 91, 123506. | 1.5 | 40 |
| 123 | Proton Radiation Effects on Nanocrystal Non-Volatile Memories. <i>IEEE Transactions on Nuclear Science</i> , 2007, 54, 975-981. | 1.2 | 5 |
| 124 | Nickel nanoparticle deposition at room temperature for memory applications. <i>Microelectronic Engineering</i> , 2007, 84, 1994-1997. | 1.1 | 33 |
| 125 | Proton radiation tolerance of nanocrystal memories. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2007, 38, 67-70. | 1.3 | 4 |
| 126 | Impact of structural parameters on the performance of silicon micromachined capacitive pressure sensors. <i>Sensors and Actuators A: Physical</i> , 2007, 137, 20-24. | 2.0 | 3 |

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|-----|--|-----|-----------|
| 127 | Laser annealing for n+/p junction formation in germanium. <i>Materials Science in Semiconductor Processing</i> , 2006, 9, 644-649. | 1.9 | 30 |
| 128 | Laser annealing of plasma implanted boron for ultra-shallow junctions in Silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006, 253, 13-17. | 0.6 | 5 |
| 129 | Capacitive pressure sensors and switches fabricated using strain compensated SiGeB. <i>Microelectronic Engineering</i> , 2006, 83, 1209-1211. | 1.1 | 7 |
| 130 | Metal nano-floating gate memory devices fabricated at low temperature. <i>Microelectronic Engineering</i> , 2006, 83, 1563-1566. | 1.1 | 26 |
| 131 | Materials Science Issues for the Fabrication of Nanocrystal Memory Devices by Ultra Low Energy Ion Implantation. <i>Defect and Diffusion Forum</i> , 2006, 258-260, 531-541. | 0.4 | 8 |
| 132 | Combination of integrated thermal flow and capacitive pressure sensors for high sensitivity flow measurements in both laminar and turbulent regions. <i>Journal of Physics: Conference Series</i> , 2005, 10, 277-280. | 0.3 | 0 |
| 133 | A Si/SiGe MOSFET utilizing low-temperature wafer bonding. <i>Microelectronic Engineering</i> , 2005, 78-79, 244-247. | 1.1 | 1 |
| 134 | Recent advances in nanoparticle memories. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 93-101. | 1.7 | 57 |
| 135 | Interstitial injection during oxidation of very low energy nitrogen-implanted silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 314-318. | 1.7 | 1 |
| 136 | Injection of point defects during annealing of low energy As implanted silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005, 124-125, 261-265. | 1.7 | 1 |
| 137 | Size and aerial density distributions of Ge nanocrystals in a SiO ₂ layer produced by molecular beam epitaxy and rapid thermal processing. <i>Applied Physics A: Materials Science and Processing</i> , 2005, 81, 363-366. | 1.1 | 8 |
| 138 | Field effect devices with metal nanoparticles integrated by Langmuir-Blodgett technique for non-volatile memory applications. <i>Journal of Physics: Conference Series</i> , 2005, 10, 57-60. | 0.3 | 5 |
| 139 | Oxidation of nitrogen-implanted silicon: Comparison of nitrogen distribution and electrical properties of oxides formed by very low and medium energy N ₂ ⁺ implantation. <i>Journal of Applied Physics</i> , 2004, 96, 300-309. | 1.1 | 8 |
| 140 | Gold Langmuir-Blodgett deposited nanoparticles for non-volatile memories. <i>Materials Research Society Symposia Proceedings</i> , 2004, 830, 317. | 0.1 | 1 |
| 141 | Ge nanocrystals in MOS-memory structures produced by molecular-beam epitaxy and rapid-thermal processing. <i>Materials Research Society Symposia Proceedings</i> , 2004, 830, 288. | 0.1 | 0 |
| 142 | Nitrogen distribution during oxidation of low and medium energy nitrogen-implanted silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004, 216, 75-79. | 0.6 | 0 |
| 143 | Nanocrystals manufacturing by ultra-low-energy ion-beam-synthesis for non-volatile memory applications. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2004, 216, 228-238. | 0.6 | 45 |
| 144 | Silicon nanocrystal memory devices obtained by ultra-low-energy ion-beam synthesis. <i>Solid-State Electronics</i> , 2004, 48, 1511-1517. | 0.8 | 65 |

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|-----|--|-----|-----------|
| 145 | Low temperature wafer bonding for thin silicon film transfer. Sensors and Actuators A: Physical, 2004, 110, 401-406. | 2.0 | 16 |
| 146 | Capacitive-type chemical sensors using thin silicon/polymer bimorph membranes. Sensors and Actuators B: Chemical, 2004, 103, 392-396. | 4.0 | 25 |
| 147 | Fabrication of chemical sensors based on Si/polymer bimorphs. Microelectronic Engineering, 2004, 73-74, 847-851. | 1.1 | 6 |
| 148 | Effects of annealing conditions on charge storage of Si nanocrystal memory devices obtained by low-energy ion beam synthesis. Microelectronic Engineering, 2003, 67-68, 629-634. | 1.1 | 11 |
| 149 | MOS memory structures by very-low-energy-implanted Si in thin SiO ₂ . Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 14-18. | 1.7 | 38 |
| 150 | Effect of ion energy and dose on the positioning of 2D-arrays of Si nanocrystals ion beam synthesised in thin SiO ₂ layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 204-207. | 1.7 | 27 |
| 151 | Effect of ion energy and dose on the positioning of 2D-arrays of Si nanocrystals ion beam synthesized in thin SiO ₂ layers. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 513-515. | 1.3 | 11 |
| 152 | Structural and electrical properties of silicon dioxide layers with embedded germanium nanocrystals grown by molecular beam epitaxy. Applied Physics Letters, 2003, 82, 1212-1214. | 1.5 | 110 |
| 153 | Langmuir-Blodgett Film Deposition of Metallic Nanoparticles and Their Application to Electronic Memory Structures. Nano Letters, 2003, 3, 533-536. | 4.5 | 279 |
| 154 | Influence of implantation energy on the electrical properties of ultrathin gate oxides grown on nitrogen implanted Si substrates. Applied Physics Letters, 2003, 82, 4764-4766. | 1.5 | 5 |
| 155 | Transmission electron microscopy measurements of the injection distances in nanocrystal-based memories. Applied Physics Letters, 2003, 82, 200-202. | 1.5 | 54 |
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